

2SC4627J

Silicon NPN epitaxial planer type

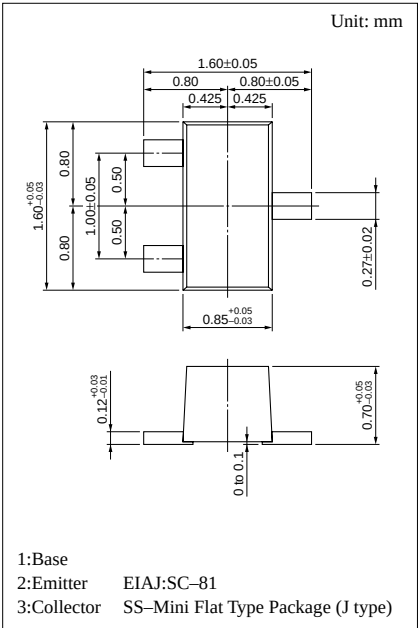
For high-frequency amplification

■ Features

- Optimum for RF amplification of FM/AM radios.
- High transition frequency f_T .
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing. (Flat type)

■ Absolute Maximum Ratings (Ta=25°C)

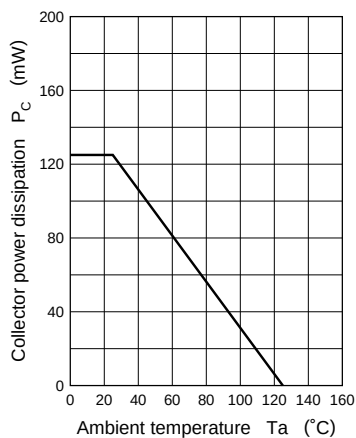
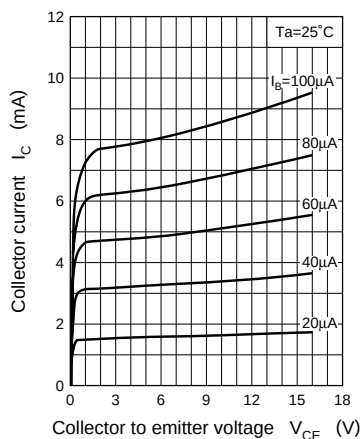
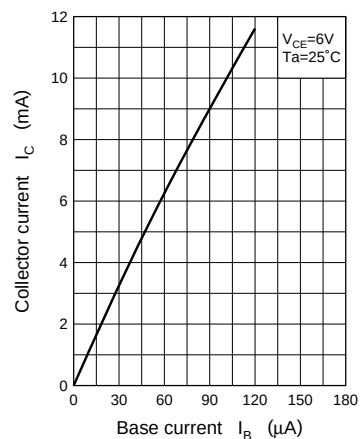
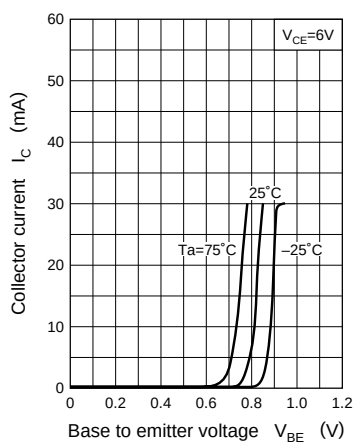
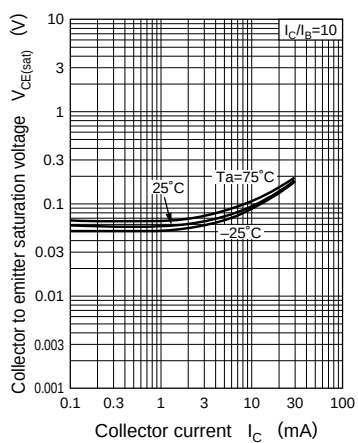
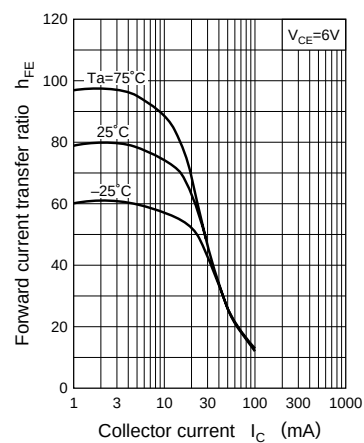
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	15	mA
Collector power dissipation	P_C	125	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 ~ +125	°C



Marking symbol : U

■ Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V_{CBO}	$I_C = 10\mu A, I_E = 0$	30			V
Emitter to base voltage	V_{EBO}	$I_E = 10\mu A, I_C = 0$	3			V
Forward current transfer ratio	h_{FE}	$V_{CB} = 6V, I_E = -1mA$	40		260	
Base to emitter voltage	V_{BE}	$V_{CB} = 6V, I_E = -1mA$		720		mV
Common emitter reverse transfer capacitance	C_{re}	$V_{CB} = 6V, I_E = -1mA, f = 10.7MHz$		0.8	1	pF
Transition frequency	f_T	$V_{CB} = 6V, I_E = -1mA, f = 200MHz$		450	650	MHz
Noise figure	NF	$V_{CB} = 6V, I_E = -1mA, f = 100MHz$		3.3		dB
Power gain	PG	$V_{CB} = 6V, I_E = -1mA, f = 100MHz$		24		dB

$P_C - T_a$  $I_C - V_{CE}$  $I_C - I_B$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $C_{ob} - V_{CB}$ 